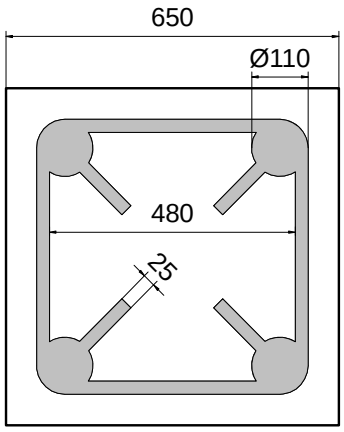
LED - Chip

ELC-875-22

26.04.2012 rev. 11

Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	N (cathode) up



LED-07

typ. dimensions (µm)

typ. thickness
180 µm

anode
gold alloy, 1.5 µm

cathode
gold alloy, 0.5 µm
structured, 25% covered

Optical and Electrical Characteristics

T_{amb} = 25℃, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		1.2	1.4	V
Forward voltage	I_F = 100 mA	V_F		1.45	1.8	V
Reverse voltage	I_R = 100 µA	V_R	5			V
Radiant power[1]	I_F = 20 mA	Φ_e	2.5	3.5		mW
Radiant power[2]	I_F = 100 mA	Φ_e		17		mW
Radiant power[3]	I_F = 100 mA	Φ_e		35		mW
Radiant intensity[1]	I_F = 20 mA	I_e	0.75	1.0		mW/sr
Peak wavelength	I_F = 100 mA	λ_p	860	875	890	nm
Spectral bandwidth at 50%	I_F = 100 mA	$\Delta\lambda_{0.5}$		45		nm
Switching time	I_F = 100 mA	t_r, t_f		20		ns

[1]Measured on bare chip on TO-18 header
[2]Measured onbare chip on TO-18 header and heat sink
[3]Measured on epoxy chip on TO-18 header and heat sink, 10s current flow (information only)

Labeling

Type	Lot N°	Φ_e(typ) [mW]	V_F(typ) [V]	Quantity
ELC-875-22				

Packing: Chips on adhesive film with wire-bond side on top

Note: All measurements carried out with JENOPTIK Polymer Systems equipment

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